

INS. A1 ~~A BUSS ARRANGEMENT FOR A DISPLAY DRIVER~~
INS B1 This invention relates generally to a buss arrangement

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15 columns and rows of an array of a display device includes semiconductor switches. Each switch has a first terminal, a second terminal and a third terminal. A first buss is coupled to a first plurality of terminals for communicating signals between the first plurality of terminals and the first terminals of the switches. Local
20 busses that are separated from one another are provided. A given local buss has a first buss section coupled to a second plurality of terminals associated with the given local buss and extends in a manner to cross over the first buss. The local buss has a second buss section extending from the first buss section has conductors coupled
25 in a local, clustering buss arrangement to the second terminals of switches associated with the given local buss. The associated switches have their third terminals coupled to consecutively disposed column conductors, respectively, of the array.

15 An arrangement, embodying an inventive feature, for transferring pixel information with respect to pixels arranged in columns and rows of an array of a display device includes semiconductor switches. Each switch has a first terminal, a second terminal and a third terminal. A first buss is coupled to a first plurality of terminals for communicating signals between the first plurality of terminals and the first terminals of the switches. Local
20 busses that are separated from one another are provided. A given local buss has a first buss section coupled to a second plurality of terminals associated with the given local buss and extends in a manner to cross over the first buss. The local buss has a second buss section extending from the first buss section has conductors coupled
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FIGURE 1 illustrates an AMLCD with integrated driver circuits, according to an aspect of the invention, when incorporating the bussing arrangement of FIGURE 3;

FIGURE 2 illustrates a prior art bussing structure; and

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FIGURE 3 illustrates a bussing structure, in accordance with an aspect of the invention, that may be incorporated in the arrangement of FIGURE 1.

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FIGURE 1 illustrates an integrated driver arrangement for storing information in an SVGA liquid crystal array. It should be understood that the invention may be utilized for storing information in pixels of a plasma display. Analog circuitry 11 receives a video signal representative of picture information to be displayed from, for example, an antenna 12. The analog circuitry 11 provides a video signal on a line 13 as an input signal to an analog-to-digital converter (A/D) 14.

The television signal from the analog circuitry 11 is to be displayed on a liquid crystal array 16 which is composed of a large number of pixel elements, such as a liquid crystal cell 16a, arranged horizontally in $m = 600$ rows and vertically in $n = 2400$ columns.

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Liquid crystal array 16 includes $n = 2400$ columns of data lines 17, one for each of the vertical columns of liquid crystal cells 16a, and $m = 600$ select lines 18, one for each of the horizontal rows of liquid crystal cells 16a.

A/D converter 14 includes an output bus 19 to provide
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brightness levels, or gray scale codes, to a memory 21 having 100 groups of output lines 22. Each group of output lines 22 of memory 21 applies the stored digital information to a corresponding digital-to-analog (D/A) converter 23. There are 100 D/A converters 23 that correspond to the 100 groups of lines 22, respectively. An output
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analog signal DBS(j) from a given D/A converter 23 is coupled via a

corresponding brightness information carrying conductor DB(j) to a demultiplexer transistor MN1 associated with a corresponding column. Transistors MN1 may be thin film transistors (TFTs). The symbol (j) assumes values from 1 to 100 associated with the 100 D/A converter 23. Demultiplexer transistor MN1 applies the information of signal DBS(j) developed on corresponding brightness information carrying conductor DB(j) to a corresponding sampling capacitor C43 for storing an analog signal VC43 in capacitor C43. Signal VC43 is coupled to a corresponding data line driver 100 that drives corresponding data line 17 associated with a corresponding column.

A select line scanner 60 produces row select signals in lines 18 for selecting, in a conventional manner, a given row of array 16. The voltages developed in 100 data lines 17 are applied during a 32 microsecond line time to pixels 16a of the selected row.

The sampling in a given group of 100 signals DBS(j) of FIGURE 1 developed in brightness information carrying conductors DB(j) occurs simultaneously under the control of a corresponding data-word pulse signal DWS(i) forming a selection word. There are 24 pulse signals DWS(i), developed on 24 separate data-word conductors DW(i), that occur successively during a 32 microsecond horizontal line time. The symbol (i) assumes values from 1 to 24 associated with the 24 separate conductors DW(i). Each pulse signal DWS(i) controls the sampling of a corresponding group of 100 signals DBS(j) in capacitors C43.

To provide an efficient time utilization, a two-stage pipeline cycle may be used. Signals DBS(j) are demultiplexed and stored in 2400 capacitors C43 by the operation of pulse signals DWS(i). Then, the information in capacitors C43 is transferred simultaneously to data line driver 100. Thus, capacitors C43 become

available for the demultiplexing of the next row information, while the previous row information is applied to the pixels.

Except for the bussing arrangement, as described later on, the circuitry of FIGURE 1 may operate, for example, similarly to that described in, for example, U.S. Patent No. 5,673,063 in the name of Sherman Weisbrod, entitled " A DATA LINE DRIVER FOR APPLYING BRIGHTNESS SIGNALS TO A DISPLAY ". A possible bussing arrangement of conductors DW(i) and DB(j) is explained in connection with FIGURE 2. The bussing arrangement of conductors DW(i) and DB(j), embodying an inventive feature, is explained in connection with FIGURE 3. Similar symbols and numerals in FIGURES 1, 2 and 3 indicate similar items or functions.

As explained before, the crossover capacitance of the input bussing structure associated with conductors DW(i) and DB(j) can be a major source of both power dissipation and yield loss, especially for higher resolution self-scanned Active Matrix Liquid Crystal Displays (AMLCDs). Long metal runs across the display and multiple crossovers (Source/Drain metal-to-Gate metal) cause significant capacitive loads, resulting in both capacitance shorting failures, unwanted crosstalk among the brightness information carrying conductors, and excessive dynamic power dissipation. The bussing arrangement of FIGURE 3 reduces the number of capacitive crossovers associated with the input buss structure thus reducing the power dissipation and improving yield.

In the bussing arrangement of FIGURE 2, all conductors DW(i), that develop gate signals DWS(i) of demultiplexer transistor MN1 of FIGURE 1, are bussed together or globally across the entire display. Each column of the array is associated with a corresponding transistor MN1 having a gate electrode connected to one of those buss conductors DW(i) via a corresponding extension conductor DWC(i).

Connection of extension conductor $DWC(i)$ to the corresponding buss conductor $DW(i)$, located closest to data scanner transistors $MN1$, does not cause excessive capacitance problem. However, making connection of a given extension conductor $DWC(i)$ to the corresponding buss conductor $DW(i)$ that is furthest away from data scanner transistors $MN1$ means that extension conductor $DWC(i)$ must cross all of the other buss conductors $DW(i)$ to which it is not connected. Capacitive coupling CP to the other conductors $DW(i)$, is incurred at each cross over as shown in FIGURE 2.

Disadvantageously, the number of capacitive crossovers increases geometrically with the number of data-word conductors $DW(i)$ according to the equation: number of crossovers = number of brightness information carrying conductors $DB(j)$ \times $1/2 \times$ (number of data-word conductors $DW(i)$). It may be desirable to reduce the number of times conductors $DWC(i)$ cross the buss of conductors $DW(i)$ so as to reduce dynamic power dissipation and improve yield.

As shown in FIGURE 3, in a "cluster bussing" buss structure, embodying an inventive feature, the brightness information carrying conductors $DB(j)$, instead of being arranged individually and uniformly across the display, are grouped together into local "clusters" such as, for example, brightness information carrying conductors $DB(1)$ - $DB(4)$. The cluster of brightness information carrying conductors $DB(1)$ - $DB(4)$ are coupled to four transistors $MN1$ having gate electrodes that share, in common, conductor $DW(24)$. In this example, the number of crossovers of brightness information carrying conductors $DB(j)$ -to-data-word conductors $DW(i)$ have been reduced by a factor of about 4:1. This, advantageously, reduces dynamic power dissipation, improves yield and reduces the crosstalk among the brightness information carrying-conductors.

In the arrangement of FIGURE 2, transistors MN1 associated with 24 adjacent columns of matrix 16 of FIGURE 1 have gates that are controlled by consecutive data-word signals DWS(i) and apply a common signal DBS(i) to the corresponding columns. In
5 comparison, in the arrangement of FIGURE 3, transistors MN1 associated with 4 adjacent columns of matrix 16 of FIGURE 1 have gates that are controlled by common data-word signal DW(24) and apply 4 different signals DBS(i) to the corresponding columns.

The cluster bussing arrangement adds a multiplicity of
10 new local sub-arrays DBSA to the bus structure. Although these new local sub-arrays do add some additional crossovers of their own (2.5 per brightness information carrying conductor), this is a small price to pay for reducing the average number of crossovers in the main brightness information carrying conductor to data-word conductor
15 matrix from 20/data-line to only 5/data-line. The total capacitive coupling in the input buss structure is thereby cut by a factor of approximately 4 using the cluster buss technique. For example: in a display with 100 DB(j) and 24 DW(i) the total number of crossovers is 28,800 using the buss technique of FIGURE 2, while cluster bussing of
20 FIGURE 3 yields 7450 total crossovers.

The primary advantages of cluster bussing, therefore, include higher yield, lower power dissipation, and reduced crosstalk. However, another advantage to cluster bussing is that we now break up the pattern of consecutive columns connected to a single signal
25 DBS(j). Small errors in signal DBS(j)-to-signal DBS(j) will normally result in noticeable "block" errors because the human eye is very sensitive to large block patterns. Using the cluster buss technique, the blocks are broken-up into a finer pitch that is, advantageously, less obvious to the viewer.

Thus, whenever demultiplexing is done with a matrix of 2 signal types involving typically 20 or more lines, the structure may be improved through the addition of clusters of sub-arrays to reduce the complexity and capacitance of the main array.

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